

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S12	14	("20030166311"   "20040005739"   "5079595"   "5296043"   "5420706"   "6057647"   "6194837").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 12:49
S14	2	"6132800".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 15:13
S15	455	((TFT or (thin near film near transistor)) same (droplet or inkjet)) and (gate same (semiconductor or active or channel)) and ((droplet or inkjet) with (active semiconductor channel or silicon or Si))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 15:33
S16	23	S15 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 15:35
S17	9	("5695658"   "5843847"   "5882538"   "6337222"   "6436229"   "6503831").PN. OR ("6972261").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/24 15:56
S18	0	"2002GB-02114247.ap., prai."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:15
S19	0	"2002GB-02114247.ap., prai."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:15

S20	0	"2002GB-0211424.7.ap, prai."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:15
S21	0	"2002GB-0211424.ap, prai."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:16
S22	559	(TFT or (thin near film near transistor)) and ((droplet or inkjet) with mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:35
S23	485	(TFT or (thin near film near transistor)) and ((droplet or inkjet) with mask\$3) and (semiconductor or active or channel) and (source with drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:37
S24	22	S23 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 16:37
S25	18628	((TFT or (thin with film with transistor)) samde (droplet or inkjet)) and ((semiconductor or active or channel) with (shape or circle or circular or oval))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:39
S26	325	((TFT or (thin with film with transistor)) same (droplet or inkjet)) and ((semiconductor or active or channel) with (shape or circle or circular or oval))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:41
S27	5	S26 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:41

S28	632	(TFT or (thin with film with transistor)) and ((droplet or inkjet) with mask\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:44
S29	64	S28 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:44
S30	1091	(TFT or (thin with film with transistor)) and ((droplet or ink\$1jet or "ink jet") with mask\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:50
S31	752	(TFT or (thin near film near transistor)) and ((droplet or ink\$1jet or "ink jet") with mask\$3) and (semiconductor or active or channel) and (source with drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:50
S32	117	S31 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:50
S33	5	09/529611	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:58
S34	5	10/068453	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 18:59
S35	16	S32 and ((drop\$3 or ink \$1jet or "ink jet") with (active or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:11

S36	273	S31 and ((drop\$3 or ink \$1jet or "ink jet") with (active or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:12
S37	16	S36 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:20
S38	235	S30 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:21
S39	48	S38 and ((drop\$3 or ink \$1jet or "ink jet") with (active or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:21
S40	161	438/159.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:21
S41	19	("20020154187"   "20040029382"   "20040266207"   "4767489"   "4943818"   "5591490"   "5695658"   "5700316"   "5843847"   "5852975"   "5882538"   "5898446"   "6196672"   "6337222"   "6386671"   "6436229"   "6503831"   "6808972"   "6872320").PN. OR ("7223700").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/24 19:35
S42	119	TFT and ((circular or oval or cylinder or cylindrical) with (semiconductor or active) near (layer or region))	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/24 19:47

S43	61	S42 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 19:48
S44	1	"10569788"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/24 21:39
S45	101	(TFT or (thin near film near transistor)) and ((semiconductor or active) with diffusion with (prevent\$3 or barrier) with (source or drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:09
S46	47	S45 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:09
S47	206	((TFT or (thin near film near transistor)) same (droplet or inkjet)).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:31
S48	25	S47 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:32
S49	368	((TFT or (thin near film near transistor)) same (droplet or ink\$1jet or "ink jet")).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:33
S50	87	S49 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:33

S51	2	"6087196".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:43
S52	7	("20040170762"   "6150668"   "6413790"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 11:54
S54	7	(amorphous with silicon with thin with film with transistor) same (ink \$1jet or "ink jet") and (wax with mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 12:16
S55	119	(TFT or (thin with film with transistor)) and (bottom near2 gate) and (ohmic near2 contact) with (source or drain) and (ink\$1jet or "ink jet" or "jet printing" or droplet or drop)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 12:35
S56	24	S55 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 12:36
S57	19	(TFT or (thin with film with transistor)) and (bottom near2 gate) and ((ohmic near2 contact) with ("n+" or doped) near (silicon or Si)) and ((ohmic near2 contact) with (metal or Cr or Ag or W or ITO))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 12:57
S58	244	(TFT or (thin with film with transistor)) and (bottom near2 gate) and ((ohmic near2 contact) with (metal or Cr or Ag or W or ITO))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 13:17

S59	131	S58 and (@ad or @rlad) < "20020830"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/25 13:18
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